

Silicon PNP Power Transistors

2SB668

**DESCRIPTION**

- With TO-220C package
- High DC current gain
- DARLINGTON

**APPLICATIONS**

- For use in power amplifier and switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter

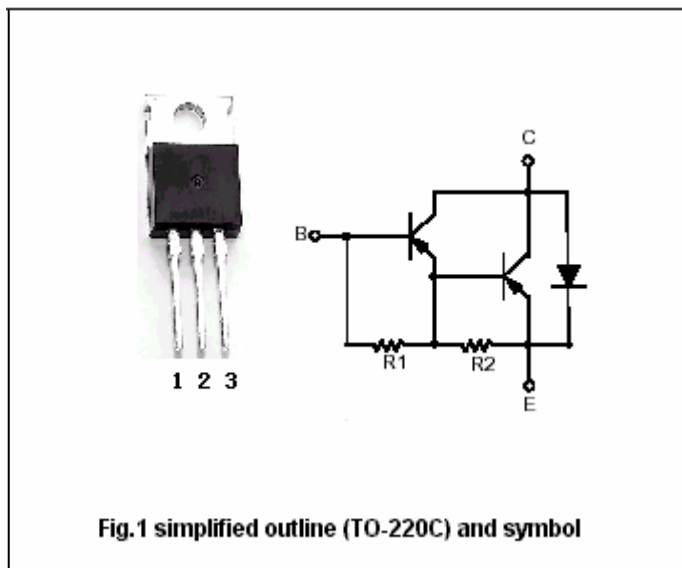


Fig.1 simplified outline (TO-220C) and symbol

**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-100	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-100	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-3	A
I <sub>CM</sub>	Collector current-peak		-5	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	25	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-100			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA, I <sub>E</sub> =0	-100			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-2mA, I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-2A, I <sub>B</sub> =-8mA			-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-2A, I <sub>B</sub> =-8mA			-2.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-120V, I <sub>E</sub> =0			-100	μA
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =-100V, I <sub>B</sub> =0			-500	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-2	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-3V	2000			

